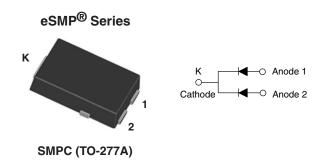
Vishay Semiconductors

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Hyperfast Rectifier, 2 x 2 A FRED Pt[®]



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I _{F(AV)}	2 x 2 A			
V _R	100 V			
V _F at I _F	0.75 V			
t _{rr (typ.)}	24 ns			
T _J max.	175 °C			
Package	SMPC (TO-277A)			
Circuit configuration	Common cathode			

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: SMPC (TO-277A)

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS compliant

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage		V _{RRM}		100	V
Average rectified forward current	per device	I	T _{Sp} = 165 °C	4	
Average rectilied forward current	per diode	IF(AV)		2	٨
Non-repetitive peak surge current	per device	1	I _{ESM} T _{.1} = 25 °C	90	A
Non-repetitive peak surge current	n-repetitive peak surge current per diode		1j=25 0	50	
Operating junction and storage terr	peratures	T _J , T _{Stg}		-65 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 100 μA	100	-	-	
Forward voltage, per diode	V _F	I _F = 2 A	-	0.88	0.95	V
		I _F = 2 A, T _J = 125 °C	-	0.75	0.82	
Reverse leakage current, per diode	I _R	$V_{R} = V_{R}$ rated	-	-	2	μA
		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	0.5	8	μΑ
Junction capacitance	CT	V _R = 100 V	-	8	-	pF

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1

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COMPLIANT

HALOGEN

FREE



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}$		-	24	-	
Reverse recovery time	+	I _F = 0.5 A, I _R = 1	A, I _{rr} = 0.25 A	-	-	24	20
Reverse recovery time	t _{rr}	T _J = 25 °C		-	16	-	ns
		T _J = 125 °C		-	22	-	
Deels receivers ourrent		T _J = 25 °C	$I_F = 2 A$	-	2	-	А
Peak recovery current I _R	I _{RRM}	T _J = 125 °C	dl _F /dt = 200 A/µs · V _B = 160 V	-	3	-	A
	0	T _J = 25 °C		-	16	-	nC
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	30	-	nC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to mount, per diode	R _{thJM}		-	4.5	5.5	°C/W
Approximate weight				0.1		g
				0.0035		oz.
Marking device		Case style SMPC (TO-277A)		JC	H1	



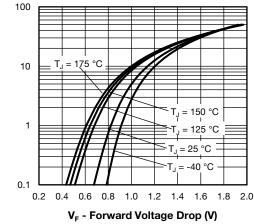


Fig. 1 - Typical Forward Voltage Drop Characteristics

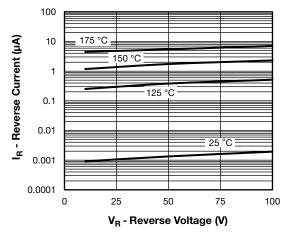
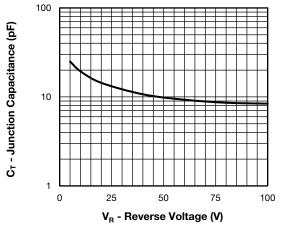


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

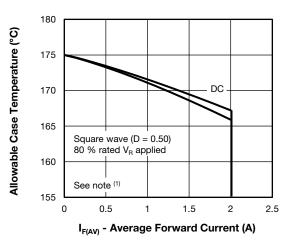


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

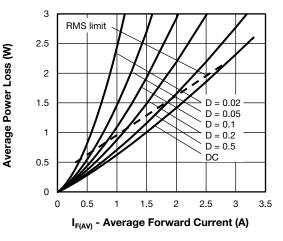
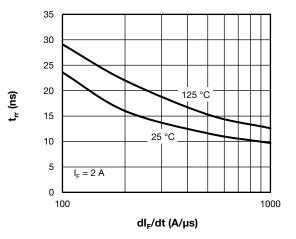


Fig. 5 - Forward Power Loss Characteristics





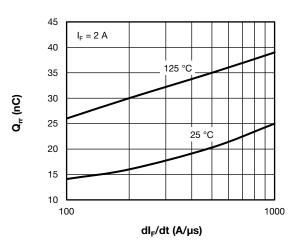


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

Revision: 13-Jan-2021

3

Document Number: 94996

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⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $[\]begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ 5); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

VS-4CSH01-M3

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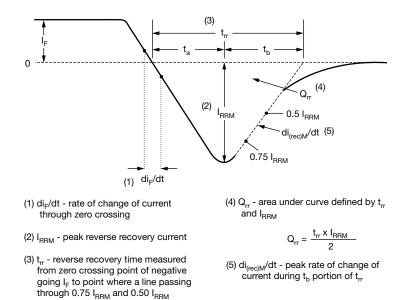
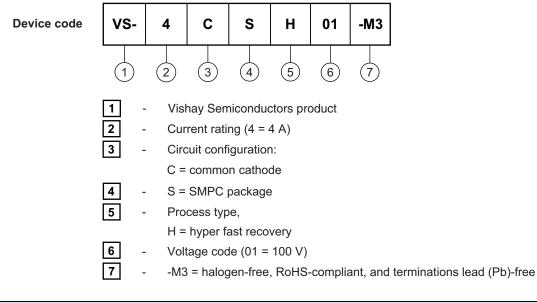


Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

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extrapolated to zero current.

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-4CSH01-M3/86A	1500	1500	7" diameter plastic tape and reel			
VS-4CSH01-M3/87A	6500	6500	13" diameter plastic tape and reel			

LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?95570				
Part marking information	www.vishay.com/doc?95565			
Packaging information	www.vishay.com/doc?88869			

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Outline Dimensions





SMPC (TO-277A)

DIMENSIONS in inches (millimeters)





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